

Microprocessor and Memory Circuits (cont'd)

ECG74S571 16-Pin DIP See Fig. D8
Schottky TTL 2K (512 x 4) PROM, 3-State Output, 55 nsec Max Access Time
 $V_{CC} = +5V$

ECG74S572 18-Pin DIP See Fig. D10
Schottky TTL 4K (1024 x 4) PROM, Open Collector Output, 60 nsec Max Access Time
 $V_{CC} = +5V$

ECG74S573 18-Pin DIP See Fig. D10
Schottky TTL 4K (1024 x 4) PROM, 3-State Output, 60 nsec Max Access Time
 $V_{CC} = +5V$

ECG2056 16-Pin DIP See Fig. D9
Digital to Analog Converter

ECG2102 16-Pin DIP See Fig. D8
NMOS 1K Static RAM (SRAM), Organized 1K by 1 Bit, 350 nsec Max Access Time. Single supply: $V_{CC} = +5V$

ECG2104 16-Pin DIP See Fig. D8
NMOS 4K Dynamic RAM (DRAM), Organized 4K by 1 Bit, 200 nsec Max Access Time. Triple Supply: $V_{CC} = +5V$, $V_{BB} = -5V$, $V_{DD} = +12V$, $V_{SS} = GND$

ECG2107 22-Pin DIP See Fig. D13
NMOS 4K Dynamic RAM (DRAM), Organized 4K by 1 Bit, 200 nsec Max Access Time. Triple Supply: $V_{CC} = +5V$, $V_{BB} = -5V$, $V_{DD} = +12V$, $V_{SS} = GND$

ECG2114 18-Pin DIP See Fig. D10
NMOS 4K Static RAM (SRAM), Organized 1K by 4 Bits, 300 nsec Max Access Time. Single Supply: $V_{CC} = +5V$

ECG2117 16-Pin DIP See Fig. D8
NMOS 16K Dynamic RAM (DRAM), Organized 16K by 1 Bit, 200 nsec Max Access Time. Triple Supply: $V_{CC} = +5V$, $V_{BB} = -5V$, $V_{DD} = +12V$, $V_{SS} = GND$

ECG2128 24-Pin DIP See Fig. D15
NMOS 16K Static RAM (SRAM), Organized 2K by 8 Bits, 150 nsec Max Access Time
 $V_{CC} = +5V$

ECG2147 18-Pin DIP See Fig. D10
NMOS 4K Static RAM (SRAM), Organized 4K by 1 Bit, 55 nsec Max Access Time. Single Supply: $V_{CC} = +5V$

ECG2164 16-Pin DIP See Fig. D8
NMOS 64K Dynamic RAM (DRAM) Organized 64K by 1 Bit, 150 nsec Max Access Time, $V_{CC} = +5V$